

(19) World Intellectual Property
Organization
International Bureau



(43) International Publication Date
24 June 2004 (24.06.2004)

PCT

(10) International Publication Number
WO 2004/053930 A3

(51) International Patent Classification⁷: H01L 51/20

(21) International Application Number:
PCT/US2003/028023

(22) International Filing Date:
8 September 2003 (08.09.2003)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
10/314,591 9 December 2002 (09.12.2002) US

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(81) Designated States (*national*): AE, AG, AL, AM, AT, AU,
AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU,
CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH,
GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC,
LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW,
MX, MZ, NO, NZ, OM, PH, PL, PT, RO, RU, SC, SD, SE,
SG, SK, SL, TJ, TM, TN, TR, TT, TZ, UA, UG, UZ, VC,
VN, YU, ZA, ZM, ZW.

(84) Designated States (*regional*): ARIPO patent (GH, GM,
KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW),
Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM),
European patent (AT, BE, BG, CH, CY, CZ, DE, DK, EE,
ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PT, RO,
SE, SI, SK, TR), OAPI patent (BF, BJ, CF, CG, CI, CM,
GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

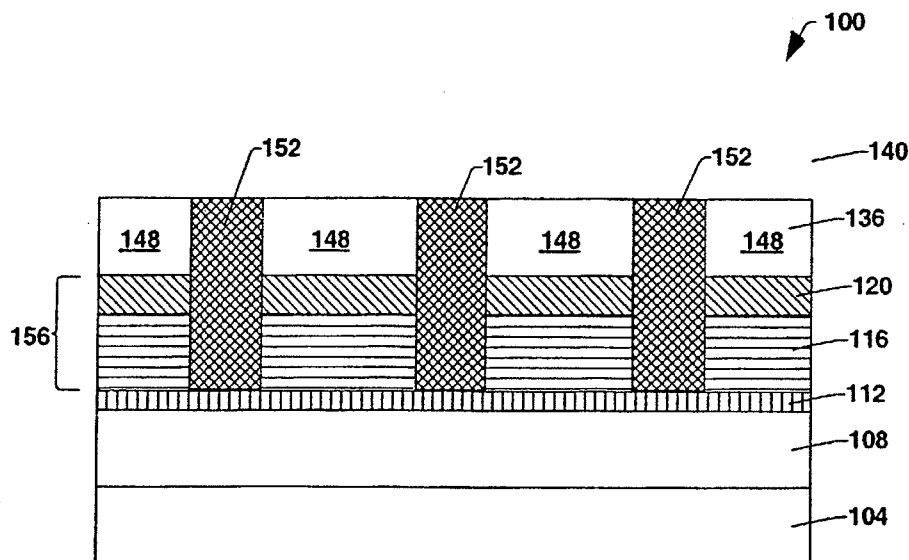
Published:

- with international search report
- before the expiration of the time limit for amending the
claims and to be republished in the event of receipt of
amendments

(88) Date of publication of the international search report:
12 August 2004

[Continued on next page]

(54) Title: SELF ALIGNED MEMORY ELEMENT AND WORDLINE



(57) Abstract: An organic polymer memory cell is provided having an organic polymer layer (116, 2108, 2132, 2168) and an electrode layer (120, 2112, 2128, 2164) formed over a first conductive (e.g., copper) layer (e.g., bitline) (104, 108). The memory cells are connected to a second conductive layer (e.g., forming a wordline) (136, 2148, 2160), and more particularly the top of the electrode layer of the memory cells to the second conductive layer. Optionally, a conductivity facilitating layer (112, 2136) is formed over the conductive layer. Dielectric material separates the memory cells. The memory cells are self-aligned with the bitlines formed in the first conductive layer and the wordlines formed in the second conductive layer.